UC1707 UC2707 UC3707

Dual Channel Power Driver

FEATURES

- Two independent Drivers
- 1.5A Totem Pole Outputs
- Inverting and Non-Inverting Inputs
- 40ns Rise and Fall into 1000pF
- High-Speed, Power MOSFET Compatible
- Low Cross-Conduction Current Spike
- Analog Shutdown with Optional Latch
- Low Quiescent Current
- 5V to 40V Operation
- Thermal Shutdown Protection
- 16-Pin Dual-In-Line Package
- 20-Pin PLCC and CLCC Package

DESCRIPTION

The UC1707 family of power drivers is made with a high-speed Schottky process to interface between low-level control functions and high-power switching devices - particularly power MOSFETs. These devices contain two independent channels, each of which can be activated by either a high or low input logic level signal. Each output can source or sink up to 1.5A as long as power dissipation limits are not exceeded.

Although each output can be activated independently with its own inputs, it can be forced low in common through the action either of a digital high signal at the Shutdown terminal or a differential low-level analog signal. The Shutdown command from either source can either be latching or not, depending on the status of the Latch Disable pin.

Supply voltage for both VIN and VC can independently range from 5V to 40V.

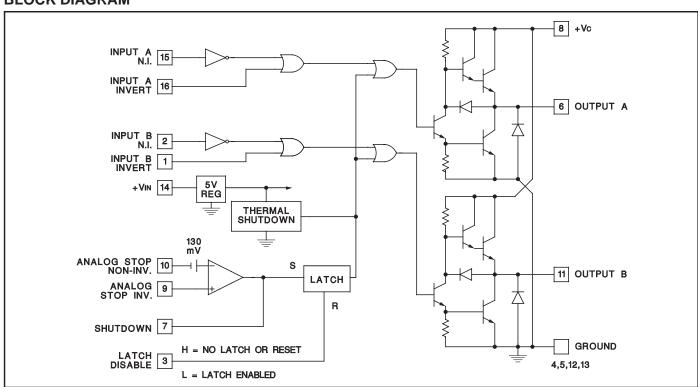
These devices are available in two-watt plastic "bat-wing" DIP for operation over a 0°C to 70°C temperature range and, with reduced power, in a hermetically sealed cerdip for -55°C to +125°C operation. Also available in surface mount DW, Q, L packages.

TRUTH TABLE (Each Channel)

INV.	N.I.	OUT
Н	Н	L
L	Н	Н
н	L	L
l	L	L

 $\overline{OUT} = \overline{INV} \text{ and N.I.}$ $\overline{OUT} = INV \text{ or N.I.}$

BLOCK DIAGRAM

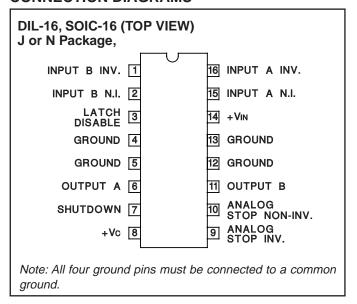


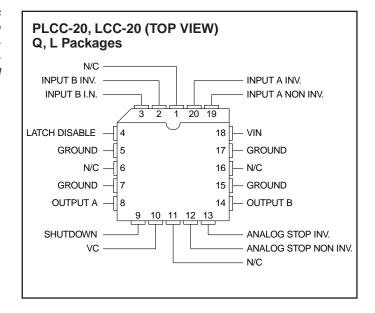
ABSOLUTE MAXIMUM RATINGS

Supply Voltage, VIN, N/J-Pkg 40V
Collector Supply Voltage, VC, N/J-Pkg40V
Output Current (Each Output, Source or Sink) Steady-State,
N/J-Pkg±500mA
Peak Transient
N-Pkg
J-Pkg
Capacitive Discharge Energy
N-Pkg
J-Pkg15mJ
Digital Inputs (See Note), N/J-Pkg 5.5V
Analog Stop Inputs, N/J-Pkg VIN
Power Dissipation at T _A = 25°C (See Note)
N-Pkg
J-Pkg
Power Dissipation at T (Leads/Case) = 25°C (See Note)
N-Pkg
J-Pkg2W
Operating Temperature Range55°C to +125°C
Storage Temperature Range65°C to +150°C
Lead Temperature (Soldering, 10 Seconds) 300°C

Note: All voltages are with respect to the four ground pins which must be connected together. All currents are positive into, negative out of the specified terminal. Digital Drive can exceed 5.5V if input current is limited to 10mA. Consult Packaging section of Databook for thermal limitations and considerations of package.

CONNECTION DIAGRAMS





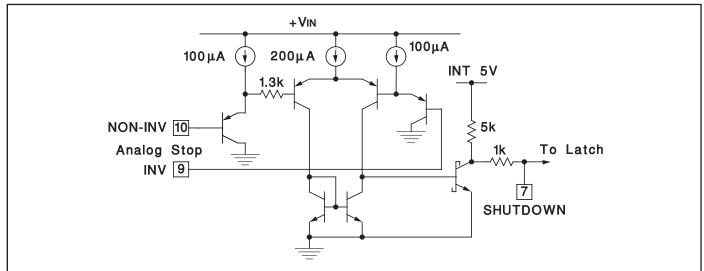
ELECTRICAL CHARACTERISTICS: Unless otherwise stated, these specifications apply for $T_A = -55^{\circ}C$ to +125°C for the UC1707, -25°C to +85°C for the UC2707 and 0°C to +70°C for the UC3707; $V_{IN} = V_C = 20V$. $T_A = T_J$.

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V _{IN} Supply Current	$V_{IN} = 40V$		12	15	mA
V _C Supply Current	$V_C = 40V$, Outputs Low		5.2	7.5	mA
V _C Leakage Current	V _{IN} =0, VC =30V, No Load		.05	0.1	mA
Digital Input Low Level				0.8	V
Digital Input High Level		2.2			V
Input Current	$V_1 = 0$		-0.06	-1.0	mA
Input Leakage	$V_1 = 5V$.05	0.1	mA
Output High Sat., V _C -V _O	$I_O = -50 \text{mA}$			2.0	V
	$I_{O} = -500 \text{mA}$			2.5	V
Output Low Sat., V _O	$I_O = -50 \text{mA}$			0.4	V
	$I_{O} = -500 \text{mA}$			2.5	V
Analog Threshold	$V_{CM} = 0$ to 15V	100	130	160	mV
Input Bias Current	$V_{CM} = 0$		-10	-20	μΑ
Thermal Shutdown			155		°C
Shutdown Threshold	Pin 7 Input	0.4	1.0	2.2	V
Latch Disable Threshold	Pin 3 Input	0.8	1.2	2.2	V

TYPICAL SWITCHING CHARACTERISTICS: $V_{IN} = V_C = 20V$, $T_A = 25$ °C. Delays measured to 10% output change.

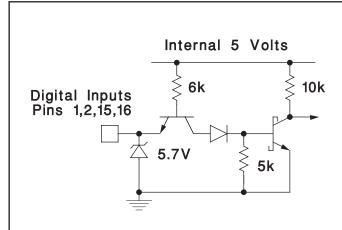
PARAMETERS	TEST CONDITIONS	OUTPUT CL =			UNITS	
From Inv. Input to Output		open	1.0	2.2	nF	
Rise Time Delay		40	50	60	ns	
10% to 90% Rise		25	40	50	ns	
Fall Time Delay		30	40	50	ns	
90% to 10% Fall		25	40	50	ns	
From N.I. Input to Output						
Rise Time Delay		30	40	50	ns	
10% to 90% Rise		25	40	50	ns	
Fall Time Delay		45	55	65	ns	
90% to 10% Fall		25	40	50	ns	
V _C Cross-Conduction	Output Rise	25			ns	
Current Spike Duration	Output Fall	0			ns	
Analog Shutdown Delay	Stop non-Inv. = 0V	180			ns	
	Stop Inv. = 0 to 0.5V	180			ns	
Digital Shutdown Delay	2V Input on Pin 7	50			ns	

SIMPLIFIED INTERNAL CIRCUITRY



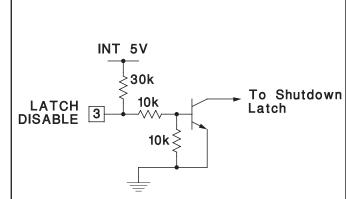
The input common-mode voltage range is from ground to (VIN-3V). When not used both inputs shoul1d be grounded. Activate time is a function of overdrive with a typical value of 180ns. Pin 7 serves both as a comparator output and as a common digital shutdown input. A high signal here will accomplish the fastest turn off of both outputs. Note that "OFF" is defined as the outputs low. Pulling shutdown low defeats the latch operation regardless of its status.

Figure 1. Typical digital input gate.



The input zener may be used to clamp input signal voltages higher than 5V as long as the zener current is limited to 10mA max. External pull-up resistors are not required.

Figure 2. Typical digital input gate.



The Shutdown latch is disabled when pin 3 is open. An impedance of 4k or less from pin 3 to ground will allow a shutdown signal to set the latch which can then be reset by either recycling the VIN supply or by momentarily (>200ns) raising pin 3 high.

Figure 3. Latch disable.

SIMPLIFIED INTERNAL CIRCUITRY (cont.)

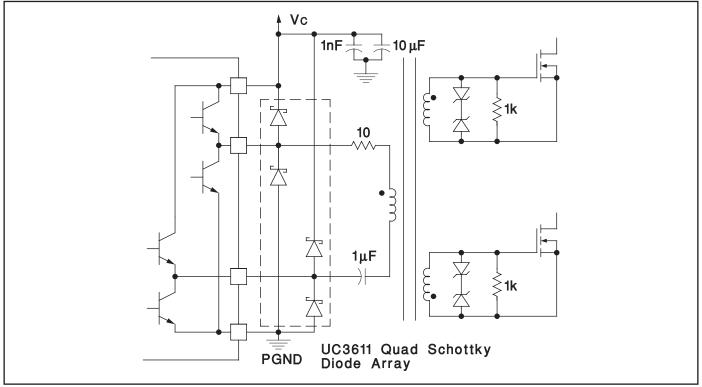


Figure 4. Transformer coupled push-pull MOSFET drive circuit.

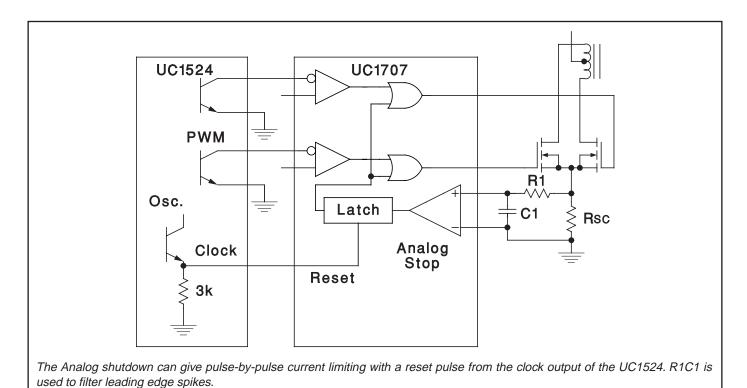
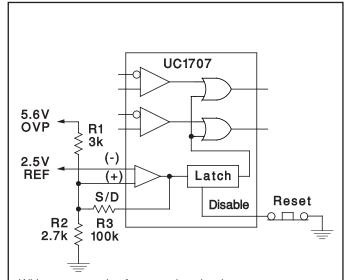


Figure 5. Current limiting.

APPLICATIONS



With an external reference, the shutdown comparator can be used for over-voltage protection. R1 and R2 set the shutdown level while R3 adds positive feedback for hysteresis.

Figure 6. Over-voltage protection.

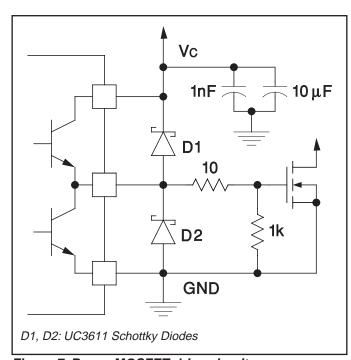
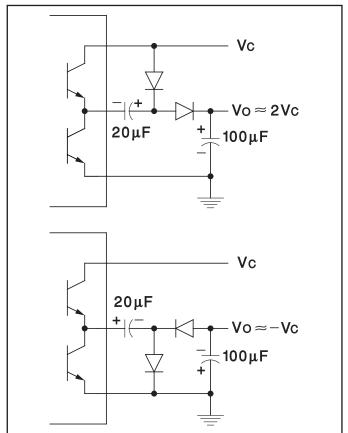


Figure 7. Power MOSFET drive circuit.



When driven with a TTL square wave drive, the low output impedance of the UC1707 allows ready implementation of charge pump voltage converters.

Figure 8. Charge pump circuits.

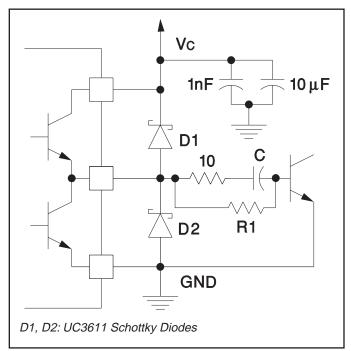


Figure 9. Power bipolar drive circuit.

TRANSFORMER COUPLING

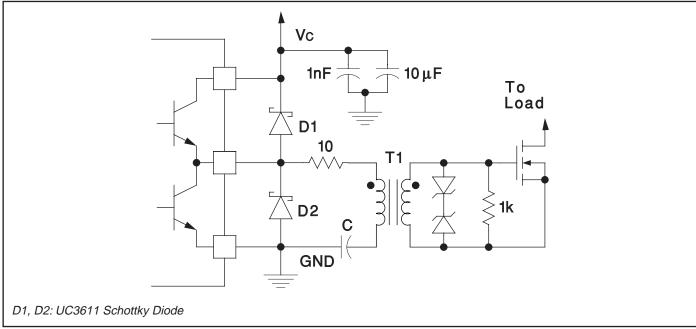


Figure 10. Transformer coupled MOSFET drive circuit.

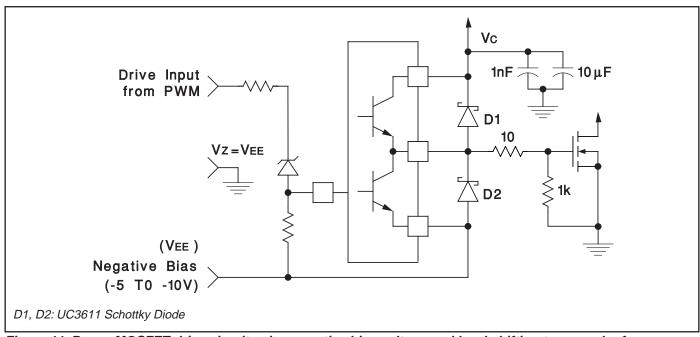


Figure 11. Power MOSFET drive circuit using negative bias voltage and level shifting to ground reference PWM.

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